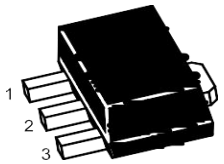
SOT-89Plastic-Encapsulate Transistors

SS8550 TRANSISTOR (PNP)



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

FEATURES

Compliment to SS8050

MARKING: Y2

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

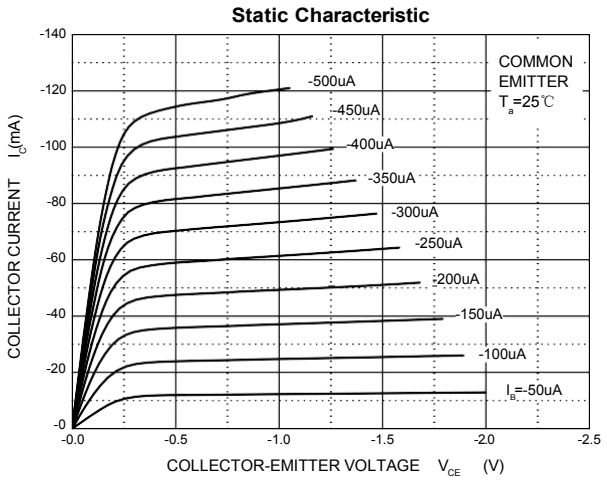
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.5	W
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	250	℃/W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

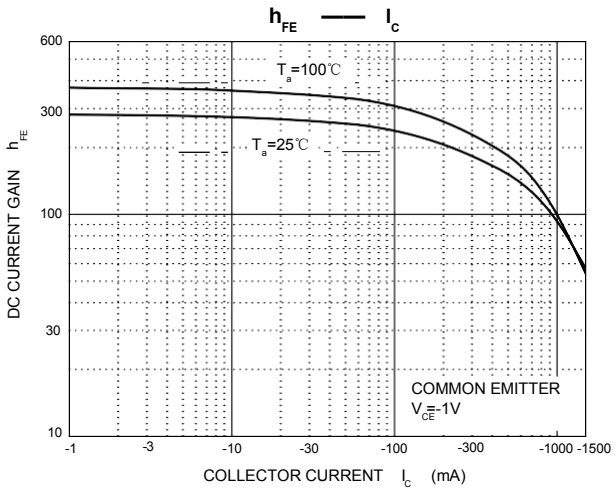
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

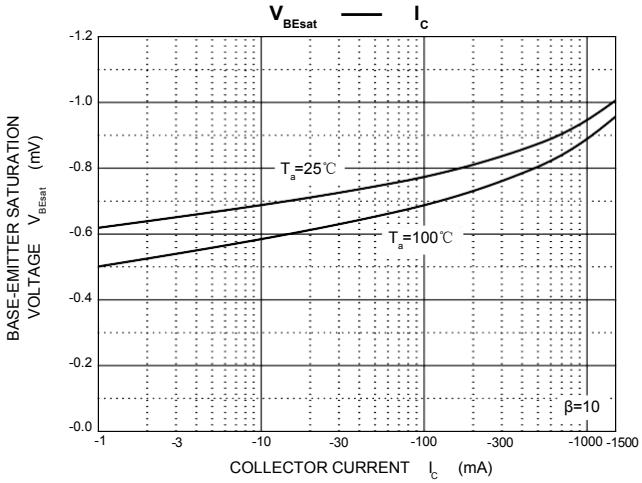
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -0.1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V,I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -100mA	120	400	
	$h_{FE(2)}$	V_{CE}= -1V, I_C= -800mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800mA, I_B= -80mA		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B= -80mA		-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	Ic=-1V,V_{CE}=-10mA		-1	V
Base-emitter positive favor voltage	V_{BEF}	I_B=-1A		-1.55	V
Transition frequency	f_T	V_{CE}= -10V, I_C= -50mA	100		MHz
output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		20	pF

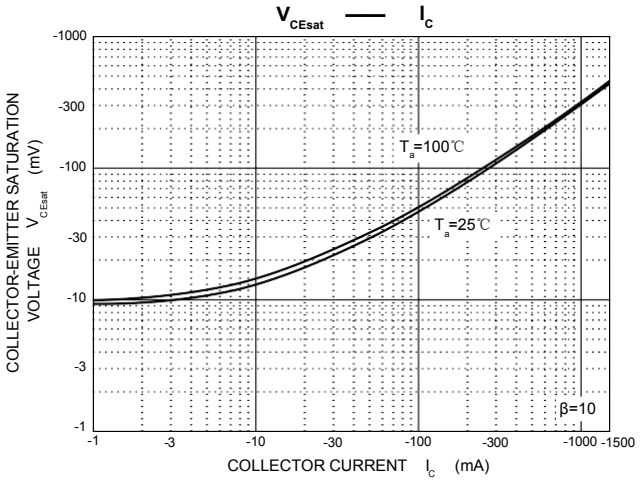
CLASSIFICATION OF $h_{FE(1)}$

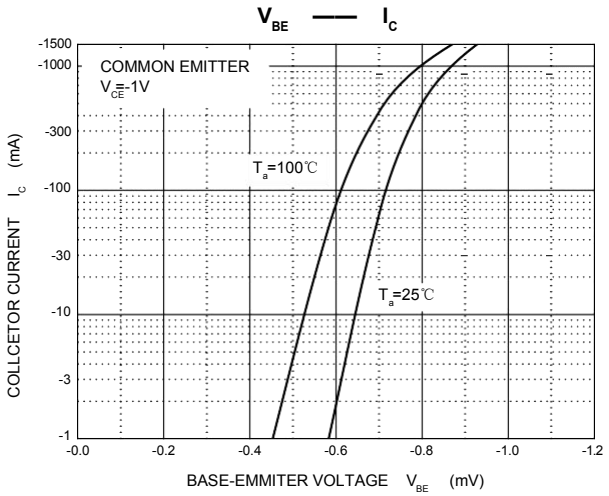
Rank	C	D	D1	D2
Range	120-200	160-300	200-350	300-400

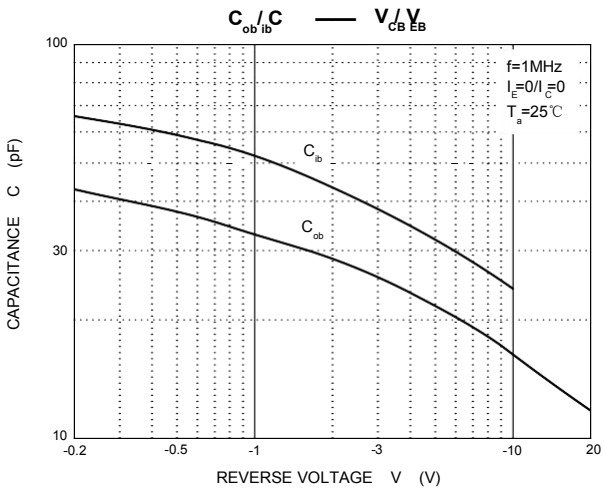

Static Characteristic
COMMON EMITTER
T_a=25℃
-500uA
-450uA
-400uA
-350uA
-300uA
-250uA
-200uA
-150uA
-100uA
I_B=-50uA
COLLECTOR CURRENT I_C(mA)
COLLECTOR-EMITTER VOLTAGE V_{CE} (V)

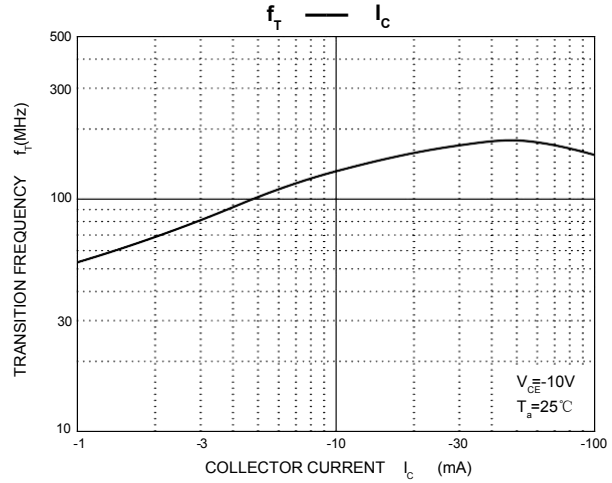

h_{FE} —— I_C
T_a=100℃
T_a=25℃
COMMON EMITTER
V_{CE}=-1V
DC CURRENT GAIN h_{FE}
COLLECTOR CURRENT I_C (mA)

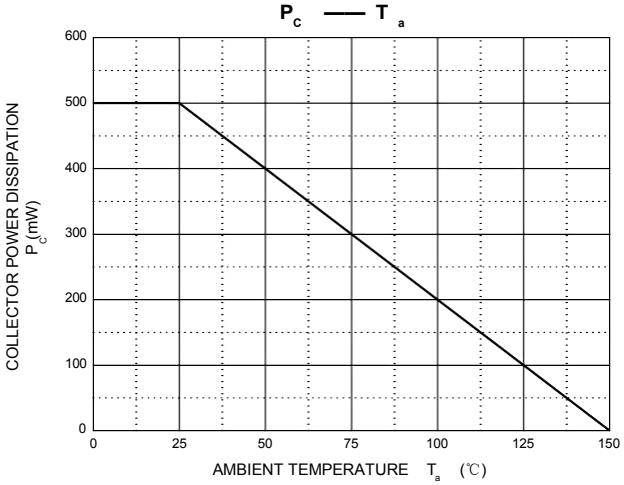

V_{BEsat} —— I_C
T_a=25℃
T_a=100℃
β=10
BASE-EMITTER SATURATION VOLTAGE V_{BEsat} (mV)
COLLECTOR CURRENT I_C (mA)


V_{CEsat} —— I_C
T_a=100℃
T_a=25℃
β=10
COLLECTOR-EMITTER SATURATION VOLTAGE V_{CEsat} (mV)
COLLECTOR CURRENT I_C (mA)


V_{BE} —— I_C
COMMON EMITTER
V_{CE}=-1V
T_a=100℃
T_a=25℃
COLLCETOR CURRENT I_C (mA)
BASE-EMMITER VOLTAGE V_{BE} (mV)

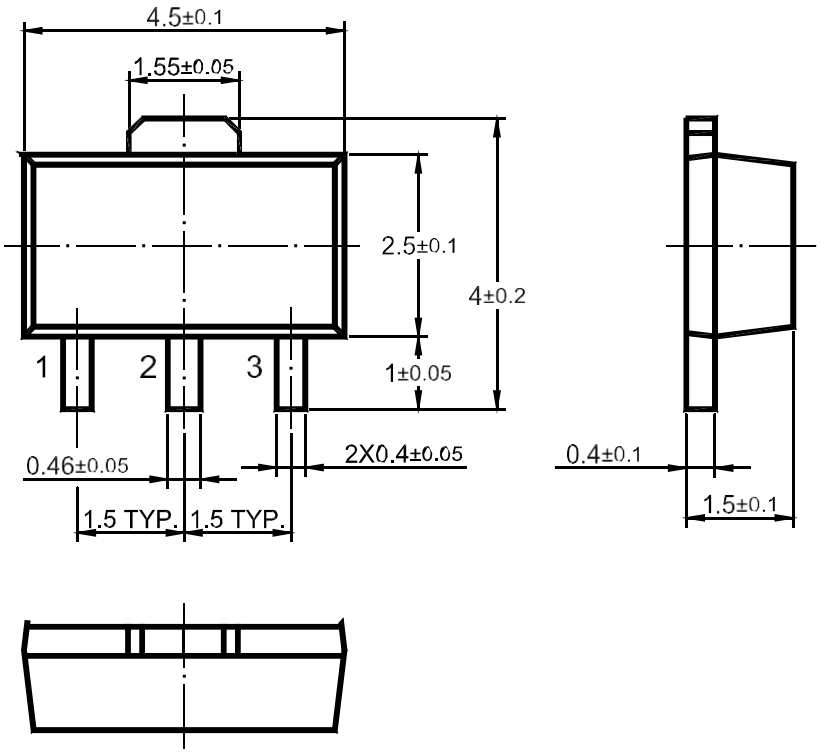

C_{ob}/C_{ib} —— V_{CB}/V_{EB}
f=1MHz
I_E=0/I_C=0
T_a=25℃
C_{ib}
C_{ob}
CAPACITANCE C (pF)
REVERSE VOLTAGE V (V)


f_T —— I_C
V_{CE}=-10V
T_a=25℃
TRANSITION FREQUENCY f_T(MHz)
COLLECTOR CURRENT I_C (mA)


P_C —— T_a
COLLECTOR POWER DISSIPATION P_C(mW)
AMBIENT TEMPERATURE T_a (℃)

SS8550

SOT-89 Package Outline Dimensions



Dimensions in mm

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